# Notification about the transfer of the semiconductor business

The semiconductor business of Panasonic Corporation was transferred on September 1, 2020 to Nuvoton Technology Corporation (hereinafter referred to as "Nuvoton"). Accordingly, Panasonic Semiconductor Solutions Co., Ltd. became under the umbrella of the Nuvoton Group, with the new name of Nuvoton Technology Corporation Japan (hereinafter referred to as "NTCJ").

In accordance with this transfer, semiconductor products will be handled as NTCJ-made products after September 1, 2020. However, such products will be continuously sold through Panasonic Corporation.

Publisher of this Document is NTCJ.

If you would find description "Panasonic" or "Panasonic semiconductor solutions", please replace it with NTCJ.

\* Except below description page

"Request for your special attention and precautions in using the technical information and semiconductors described in this book"

Nuvoton Technology Corporation Japan

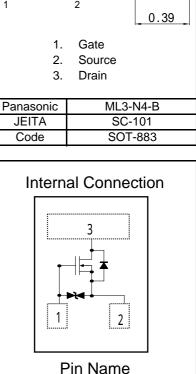


## MOS FET FK3F03080L

#### FK3F03080L Silicon N-channel MOSFET Unit : mm For switching circuits 0.6 3 Features • Low drive voltage : 2.5 V drive • Halogen-free / RoHS compliant 0 (EU RoHS / UL-94 V-0 / MSL : Level 1 compliant) Marking Symbol : X8 1 2 Packaging Embossed type (Thermo-compression sealing) : 10 000 pcs / reel (standard) Gate 1. 2. Source 3. Drain

Absolute Maximum Ratings Ta = 25 °	C					
Parameter	Symbol	Rating	Unit			
Drain to Source Voltage	VDS	30	V			
Gate to Source Voltage	VGS	±20	v			
Drain Current	ID	100	mA			
Drain Current (Pulsed) <sup>*1</sup>	IDp	200	ША			
Total Power Dissipation	PD	100	mW			
Channel Temperature	Tch	150	°C			
Storage Temperature Range	Tstg	-55 to +150	U			

Note \*1 Pulse test: Ensure that the channel temperature does not exceed 150 °C



# Gate

- 1. 2. Source
- 3. Drain

# **Panasonic**

MOS FET FK3F03080L

### ■ Electrical Characteristics Ta = 25 °C ± 3 °C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-source Breakdown Voltage	VDSS	ID = 1 mA, VGS = 0 V	30			V
Zero Gate Voltage Drain Current	IDSS	VDS = 30 V, VGS = 0 V			1	μΑ
Gate-source Leakage Current	IGSS	$VGS = \pm 16 V, VDS = 0 V$			±10	μΑ
Gate-source Threshold Voltage	Vth	ID = 6.9 μA, VDS = 10 V	0.6		2.0	V
Drain-source On-state Resistance	RDS(on)1	ID = 10 mA, VGS = 2.5 V		4.0	12	Ω
	RDS(on)2	ID = 100 mA, VGS = 4.5 V		1.0	1.4	
Input Capacitance	Ciss			11		pF
Output Capacitance	Coss	VDS = 10 V, VGS = 0 V f = 1 MHz		6.8		
Reverse Transfer Capacitance	Crss			3.5		
Turn-on Delay Time <sup>*1</sup>	ton	VDD = 3 V, VGS = 0 to 3 V ID = 10 mA, RL = 300 Ω		20		ns
Turn-off Delay Time <sup>*1</sup>	toff	VDD = 3 V, VGS = 3 to 0 V ID = 10 mA, RL = 300 Ω		100		ns

Note: 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

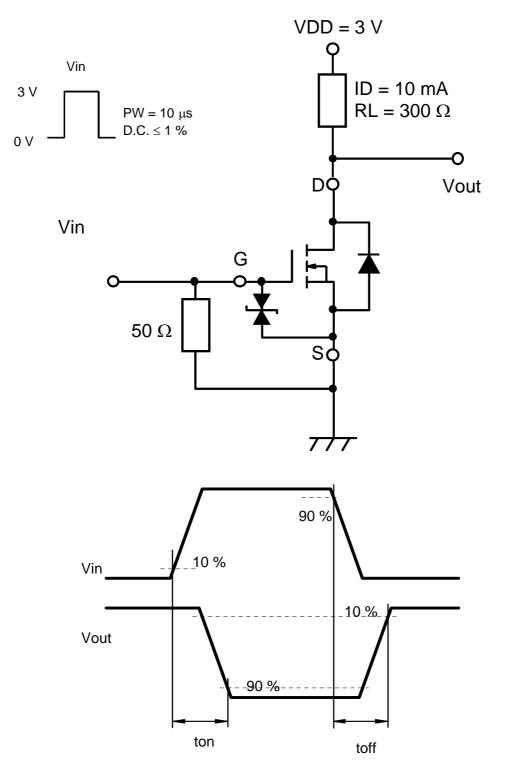
2. \*1 Measurement circuit for Turn-on Delay Time / Turn-off Delay Time

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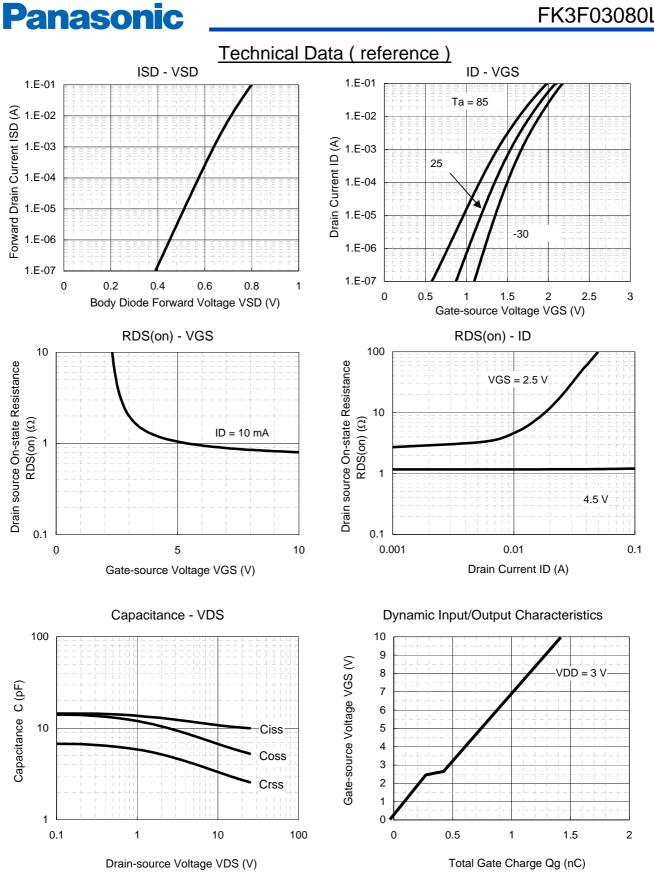
MOS FET FK3F03080L

\*1 Measurement circuit for Turn-on Delay Time / Turn-off Delay Time



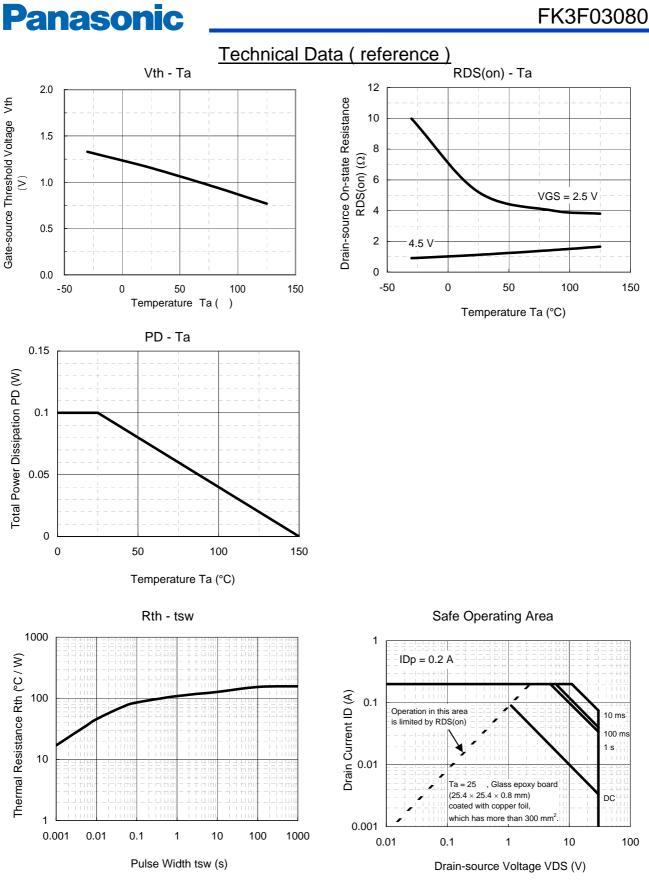
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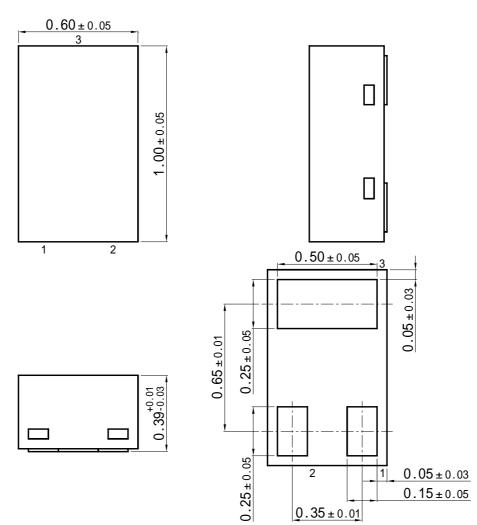




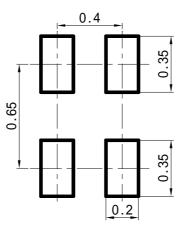


Unit : mm

ML3-N4-B



■ Land Pattern (Reference) (Unit : mm)



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